DAP222, DAP202U

Common Anode Silicon Dual Switching Diodes

These Common Anode Silicon Epitaxial Planar Dual Diodes are designed for use in ultra high speed switching applications. The DAP222 device is housed in the SC-75/SOT-416 package which is designed for low power surface mount applications, where board space is at a premium. The DAP202U device is housed in the SC-70/SOT-323 package.

Features

- Fast trr
- Low C_D
- NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS $(T_A = 25^{\circ}C)$

Rating	Symbol	Value	Unit
Reverse Voltage	V_R	80	Vdc
Peak Reverse Voltage	V_{RM}	80	Vdc
Forward Current	I _F	100	mAdc
Peak Forward Current	I _{FM}	300	mAdc
Peak Forward Surge Current	I _{FSM} (1)	2.0	Adc

THERMAL CHARACTERISTICS

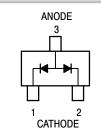
Rating	Symbol	Max	Unit
Power Dissipation	P_{D}	150	mW
Junction Temperature	T_J	150	°C
Storage Temperature	T _{stg}	-55 ~ + 150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.



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MARKING DIAGRAMS



SC-70 CASE 419





SC-75 CASE 463 STYLE 4



NB, P9 = Device Codes M = Date Code*

■ = Pb-Free Package (Note: Microdot may be in either location)

*Date Code orientation and/or orientation may vary depending upon manufacturing location.

ORDERING INFORMATION

Device	Package	Shipping [†]
DAP202UG	SC-70 (Pb-Free)	3000 / Tape & Reel
DAP222G	SC-75 (Pb-Free)	3000 / Tape & Reel
DAP222T1G	SC-75 (Pb-Free)	3000 / Tape & Reel
NSVDAP222T1G	SC-75 (Pb-Free)	3000 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

DAP222, DAP202U

ELECTRICAL CHARACTERISTICS (T_A = 25°C)

Characteristic	Symbol	Condition	Min	Max	Unit
Reverse Voltage Leakage Current	I _R	V _R = 70 V	-	0.1	μAdc
Forward Voltage	V _F	I _F = 100 mA	_	1.2	Vdc
Reverse Breakdown Voltage	V_R	I _R = 100 μA	80	-	Vdc
Diode Capacitance	C _D	$V_R = 6.0 \text{ V}, f = 1.0 \text{ MHz}$	_	3.5	pF
Reverse Recovery Time DAP222 DAP202U	t _{rr} (2) t _{tt} (3)	$I_F = 5.0$ mA, $V_R = 6.0$ V, $R_L = 100$ Ω , $I_{rr} = 0.1$ I_R $I_F = 5.0$ mA, $V_R = 6.0$ V, $R_L = 50$ Ω , $I_{rr} = 0.1$ I_R	-	4.0 10.0	ns

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

- t = 1 μS
 t_{rr} Test Circuit for DAP222 in Figure 4.
 trr Test Circuit for DAP202U in Figure 5.

TYPICAL ELECTRICAL CHARACTERISTICS

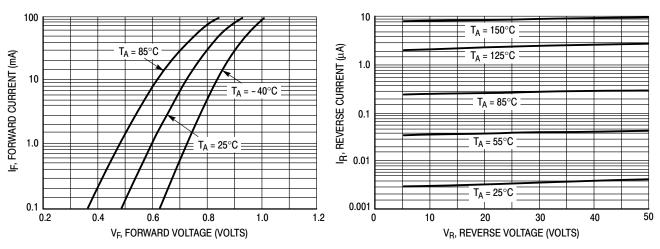


Figure 1. Forward Voltage

Figure 2. Reverse Current

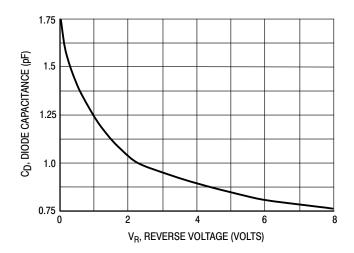


Figure 3. Diode Capacitance

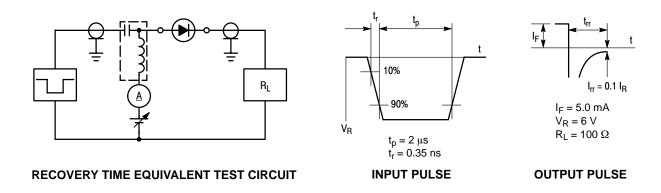


Figure 4. Reverse Recovery Time Test Circuit for the DAP222

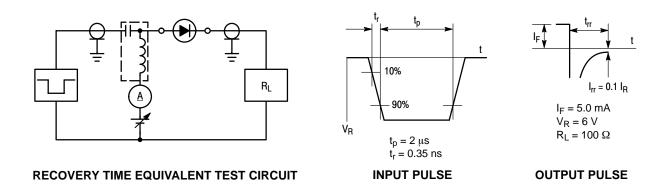


Figure 5. Reverse Recovery Time Test Circuit for the DAP202U







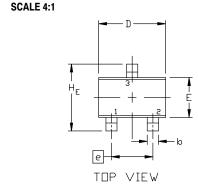
SC-70 (SOT-323) CASE 419 ISSUE R

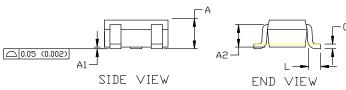
DATE 11 OCT 2022

NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1982.
- 2. CONTROLLING DIMENSION: INCH

	MILLIMETERS			INCHES		
DIM	MIN.	N□M.	MAX.	MIN.	N□M.	MAX.
Α	0.80	0.90	1.00	0.032	0.035	0.040
A1	0.00	0.05	0.10	0.000	0.002	0.004
A2	0.70 REF			0.028 BSC		
b	0.30	0.35	0.40	0.012	0.014	0.016
С	0.10	0.18	0.25	0.004	0.007	0.010
D	1.80	2.00	2.20	0.071	0.080	0.087
E	1.15	1.24	1.35	0.045	0.049	0.053
е	1.20	1.30	1.40	0.047	0.051	0.055
e1	0.65 BSC				0.026 BS	C
L	0.20	0.38	0.56	0.008	0.015	0.022
HE	2.00	2.10	2.40	0.079	0.083	0.095





GENERIC MARKING DIAGRAM

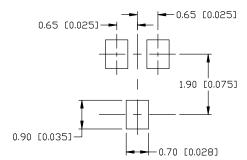


XX = Specific Device Code

M = Date Code

■ = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.



For additional information on our Pb-Free strategy and soldering details, please download the IIN Semiconductor Soldering and Mounting Techniques Reference Manual, SDLDERRM/D.

SOLDERING FOOTPRINT

STYLE 1: CANCELLED	STYLE 2: PIN 1. ANODE 2. N.C. 3. CATHODE	STYLE 3: PIN 1. BASE 2. EMITTER 3. COLLECTOR	STYLE 4: PIN 1. CATHODE 2. CATHODE 3. ANODE	STYLE 5: PIN 1. ANODE 2. ANODE 3. CATHODE	
STYLE 6:	STYLE 7:	STYLE 8:	STYLE 9:	STYLE 10:	STYLE 11:
PIN 1. EMITTER	PIN 1. BASE	PIN 1. GATE	PIN 1. ANODE	PIN 1. CATHODE	PIN 1. CATHODE
2. BASE	2. EMITTER	2. SOURCE	2. CATHODE	2. ANODE	CATHODE
COLLECTOR	COLLECTOR	3. DRAIN	CATHODE-ANODE	3. ANODE-CATHODE	CATHODE

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DESCRIPTION:	SC-70 (SOT-323)		PAGE 1 OF 1	

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SC75-3 1.60x0.80x0.80, 1.00P

CASE 463 ISSUE H

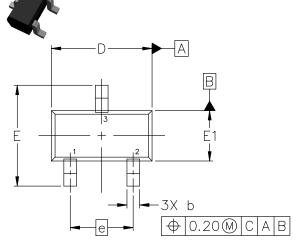
DATE 01 FEB 2024

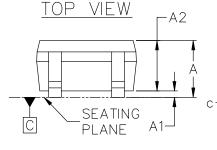
NOTES:

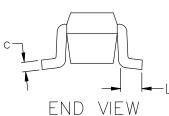
- DIMENSIONING AND TOLERANCING CONFORM TO ASME Y14.5-2018.
- ALL DIMENSION ARE IN MILLIMETERS.

DIM	MILLIMETERS				
	MIN.	NOM.	MAX.		
А	0.70	0.80	0.90		
A1	0.00	0.05	0.10		
A2	0.80 REF.				
b	0.15	0.20	0.30		
С	0.10	0.15	0.25		
D	1.55	1.60	1.65		
Е	1.50	1.60	1.70		
E1	0.70	0.80	0.90		
е	1.00 BSC				
L	0.10	0.15	0.20		

-0.356







SIDE VIEW

GENERIC MARKING DIAGRAM*



XX = Specific Device Code

Μ = Date Code

= Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "=", may or may not be present. Some products may not follow the Generic Marking.

STYLE 1:	
PIN 1. BASE	
O EMITTED	

STYLE 4: PIN 1. CATHODE 2. CATHODE 3. ANODE

3. COLLECTOR

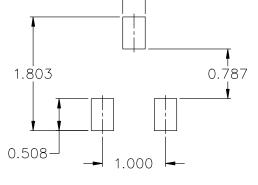
STYLE 2: PIN 1. ANODE 2. N/C 3. CATHODE

STYLE 5: PIN 1. GATE 2. SOURCE 3. DRAIN

STYLE 3: PIN 1. ANODE 2. ANODE 3 CATHODE

RECOMMENDED MOUNTING FOOTPRINT* FOR ADDITIONAL INFORMATION ON OUR Pb-FREE STRATEGY

AND SOLDERING DETAILS, PLEASE DOWNLOAD THE ON SEMICONDUCTOR SOLDERING AND MOUNTING TECHNIQUES REFERENCE MANUAL, SOLDERRM/D.



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DESCRIPTION:

SC75-3 1.60x0.80x0.80, 1.00P

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